

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for fabricating a film, the method comprising:

supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 90 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form ~~the reactive-species~~plasma.

2. (Original) The method of claim 1, said energy being supplied to the gas mixture by electric power in a frequency range of 1 kHz to 100 MHz.

3. (Original) The method of claim 1, one of helium, argon, neon krypton, xenon or one of a mixture of at least two chosen from a group consisting of helium, argon neon, krypton and xenon being used as noble gas.

4. (Original) The method of claim 1, temperature of the substrate on which said film is to be formed being in a range of 25 to 500°C.

5. (Original) The method of claim 1, the film being silicon dioxide or having a composition close to silicon dioxide.

6. (Original) The method of claim 1, the film being silicon nitride or having a composition close to silicon nitride.

7. (Original) The method of claim 1, the film being one of a silicon film, a doped silicon film, and a hydrogenated-silicon film.

8. (Original) The method of claim 1, the film being one of a metal and an alloy film.

9. (Original) A semiconductor device comprising a film fabricated according to the method of claim 1.

10. (Original) The semiconductor device of claim 9, the semiconductor device being one of a metal oxide semiconductor field effect transistor device, a thin film transistor, and a silicon on insulator device.

11. (Original) The semiconductor device of claim 9, the semiconductor device being a photovoltaic device.

12. (Original) An electro-optical apparatus comprising the semiconductor device of claim 9.

13. (Original) A memory device comprising a film fabricated according to the method of claim 1.

14. (Original) The memory device of claim 13, the memory device being one of a metal oxide semiconductor field effect transistor device, a thin film transistor, and a silicon on insulator device.

15. (Original) The memory device of claim 13, the memory device being a photovoltaic device.

16. (Currently Amended) A method for fabricating a film, the method comprising:

supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 1 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form ~~the reactive species~~ plasma.

17. (Currently Amended) A method for fabricating a film, the method comprising:

supplying optical energy with a light of wavelength less than 200 nanometer to a mixture of noble gas and reactant gas to create reactive species, the reactive species forming a film on a substrate, the ~~electrical-optical~~ energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form ~~the reactive-species~~plasma.

18. (Original) A semiconductor device comprising a film fabricated according to the method of claim 17.

19. (Original) A memory device comprising a film fabricated according to the method of claim 17.

20. (Currently Amended) A method for fabricating a semiconductor device, the method comprising:

a step of forming a film by supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 90 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form ~~the reactive-species~~plasma.

21. (Currently Amended) A method for fabricating a memory device, the method comprising:

a step of forming a film by supplying electrical energy to a mixture of noble gas and reactant gas at a total pressure of 90 kPa to 110 kPa to create reactive species, the reactive species forming a film on a substrate, the electrical energy being used for producing noble gas radicals and ions, the noble gas radicals and ions colliding with the reactant gas to form ~~the reactive-species~~plasma.

22. (Currently Amended) A method for fabricating a film according to claim 2, the electric power being applied ~~through~~ between electrodes, the distance between the electrodes being less than 5mm.